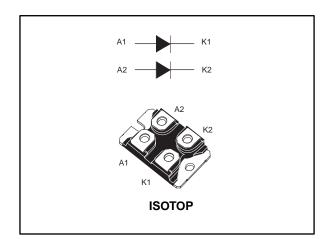


## **STPS160H100TV**

## High voltage power Schottky rectifier

Datasheet - production data



#### **Features**

- Negligible switching losses
- High junction temperature capability
- Low leakage current
- Good trade-off between leakage current and forward voltage drop
- Avalanche rated
- Low induction package
- Insulated package ISOTOP:
  - Insulated voltage: 2500 V<sub>RMS</sub>
  - Capacitance: 45 pF

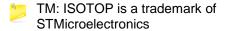
#### **Description**

High frequency dual Schottky rectifier designed for high frequency telecom, computer SMPS and other power converters.

Packaged in ISOTOP, this device is intended for use in medium voltage operation and in high frequency circuitries where low switching losses and low noise are required.

**Table 1: Device summary** 

Symbol	Value
I <sub>F(AV)</sub>	2 x 80 A
V <sub>RRM</sub>	100 V
T <sub>j</sub> (max.)	150 °C
V <sub>F</sub> (max.)	0.68 V



Characteristics STPS160H100TV

## 1 Characteristics

Table 2: Absolute ratings (limiting values, per diode)

Symbol	Parameter	Value	Unit		
V <sub>RRM</sub>	Repetitive peak reverse voltage			100	V
I <sub>F(RMS)</sub>	Forward rms current			180	Α
I <sub>F(AV)</sub>	Average forward current, δ = 0.5	T <sub>C</sub> = 110 °C Per diode Per device		80 160	Α
I <sub>FSM</sub>	Surge non repetitive forward current	t <sub>p</sub> = 10 ms sinusoidal		1000	Α
I <sub>RRM</sub>	Repetitive peak reverse current	t <sub>p</sub> = 2 μs square f = 1 kHz		2	Α
I <sub>RSM</sub>	Non repetitive peak reverse current	t <sub>p</sub> = 100 μs square		10	Α
Parm	Repetitive peak avalanche power	t <sub>p</sub> = 10 μs T <sub>j</sub> = 125 °C		5400	W
T <sub>stg</sub>	Storage temperature range			-55 to +150	°C
$T_{j}$	Maximum operating junction temperature <sup>(1)</sup>			150	°C

#### Notes:

**Table 3: Thermal parameters** 

Symbol	Parameter Maximum values			
D	lunation to again	Per diode	0.9	
R <sub>th(j-c)</sub>	Junction to case	Total		°C/W
R <sub>th(c)</sub>	Coupling	0.14		

When the diodes 1 and 2 are used simultaneously:

 $\Delta T_{j} \left( diode1 \right) = P_{\left( diode1 \right)} \, x \, \, R_{th\left( j\text{-}c \right)} \left( per \, diode \right) \, + \, P_{\left( diode2 \right)} \, x \, \, R_{th\left( c \right)}$ 

 $<sup>^{(1)}(</sup>dP_{tot}/dT_j) < (1/R_{th(j\text{-}a)}) \text{ condition to avoid thermal runaway for a diode on its own heatsink.}$ 

STPS160H100TV Characteristics

**Table 4: Static electrical characteristics** 

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I <sub>R</sub> <sup>(1)</sup>	. (1)	T <sub>j</sub> = 25 °C	., .,	-		40	μΑ
IR''	Reverse leakage current	T <sub>j</sub> = 125 °C	$V_R = V_{RRM}$	ı	13	50	mA
	V <sub>F</sub> <sup>(2)</sup> Forward voltage drop	T <sub>j</sub> = 25 °C	I <sub>F</sub> = 60 A	-		0.75	
		T <sub>j</sub> = 125 °C		ı	0.59	0.63	
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 80 A	ı		0.80	
V <sub>-</sub> (2)		T <sub>j</sub> = 125 °C		ı	0.63	0.68	V
VF(=)		T <sub>j</sub> = 25 °C	1 400 A	ı		0.87	V
	T <sub>j</sub> = 125 °C	I <sub>F</sub> = 120 A	ı	0.69	0.74		
		T <sub>j</sub> = 25 °C	I <sub>F</sub> = 160 A	-		0.92	
		T <sub>j</sub> = 125 °C		ı	0.75	0.80	

#### Notes:

 $^{(1)}$ Pulse test: t<sub>p</sub> = 5 ms,  $\delta$  < 2%

 $^{(2)}\text{Pulse}$  test:  $t_p$  = 380  $\mu\text{s},\,\delta$  < 2%

To evaluate the maximum conduction losses, use the following equation:

 $P = 0.56 \text{ x } I_{F(AV)} + 0.0015 \text{ x } I_{F^2(RMS)}$ 

Characteristics STPS160H100TV

### 1.1 Characteristics (curves)

Figure 1: Conduction losses versus average

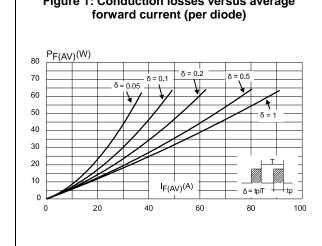


Figure 2: Forward voltage drop versus forward current (δ = 0.5, per diode)

100

|F(AV)(A)
| Rth(j-a) = Rth(j-c) | Rth(j-a) = 2 °C/W | Rth(j-a) =

Figure 3: Normalized avalanche power derating versus pulse duration

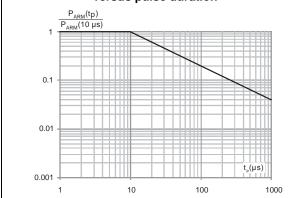


Figure 4: Relative variation of thermal impedance junction versus pulse duration (per diode)

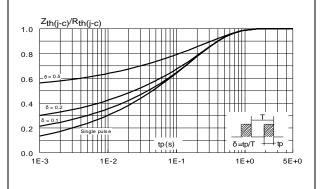


Figure 5: Reverse leakage current versus reverse voltage applied (typical values, per diode)

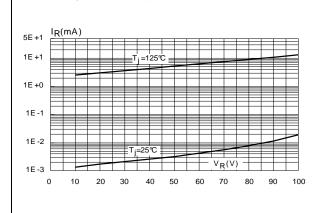
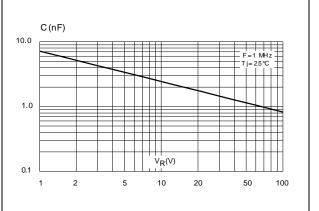


Figure 6: Junction capacitance versus reverse voltage applied (typical values, per diode)



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STPS160H100TV Characteristics

Package information STPS160H100TV

### 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

• Epoxy meets UL94, V0

Cooling method: by conduction (C)
 Recommended torque value: 1.3 N·m

Maximum torque value: 1.5 N⋅m

STMicroelectronics strongly recommends the use of the screws delivered with this product.

The use of any other screws is entirely at the user's own risk and will invalidate the warranty.



STPS160H100TV Package information

# 2.1 ISOTOP package information

Figure 8: ISOTOP package outline

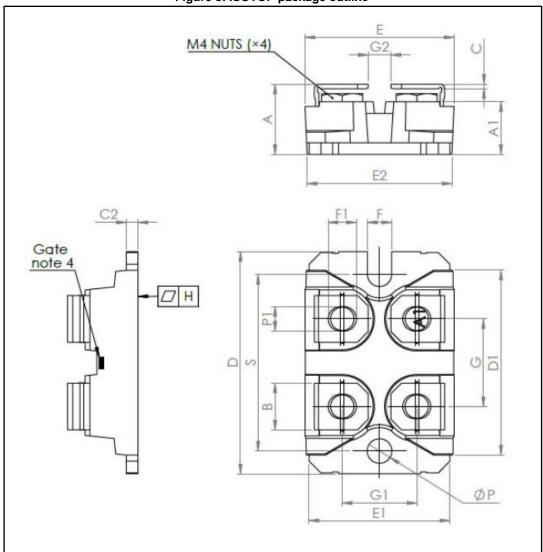


Table 5: ISOTOP package mechanical data

	Dimensions			
Ref.	Millimeters		Inch	ies
	Min.	Max.	Min.	Max.
Α	11.80	12.20	0.460	0.480
A1	8.90	9.10	0.350	0.358
В	7.80	8.20	0.307	0.323
С	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
Е	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80		0.97	76
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5	0.181	0.197
Н	-0.05	0.1	-0.002	0.004
Diam P	4	4.30	0.157	0.169
P1	4	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

STPS160H100TV Ordering information

# 3 Ordering information

**Table 6: Ordering information** 

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STPS160H100TV	STPS160H100TV	ISOTOP	27 g (without screws)	10 (with screws)	Tube

# 4 Revision history

**Table 7: Document revision history** 

Date	Revision	Changes
Jul-2003	3a	Last release.
06-Jun-2017	4	Updated Section 2.1: "ISOTOP package information".
24-Nov-2017	5	Updated Table 5: "ISOTOP package mechanical data".

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